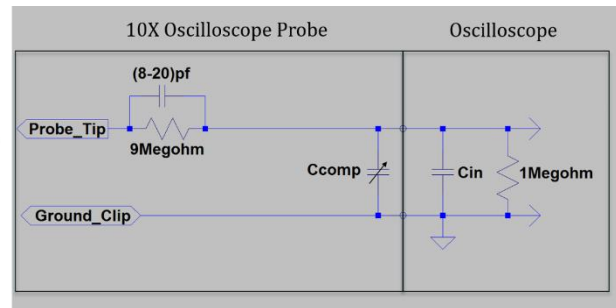
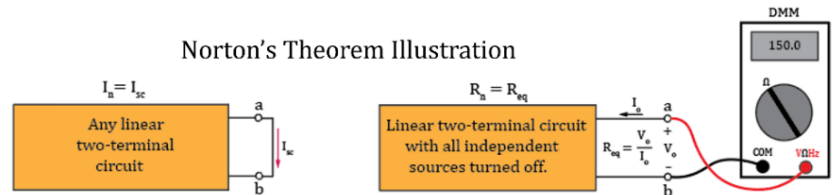
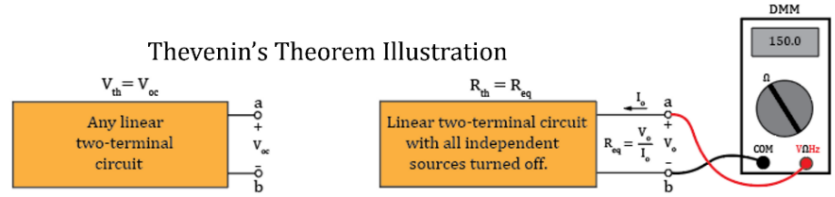
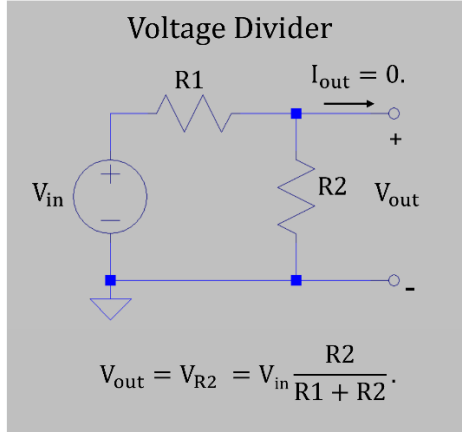


ECEN 350 – Equation Sheet 1 (9/09/2024)

Capacitor Impedance: $Z_C = X_C \angle (-90^\circ) = -jX_C$, with $X_C = 1/\omega C = 1/2\pi fC$.

Inductor Impedance: $Z_L = X_L \angle 90^\circ = jX_L$, with $X_L = \omega L = 2\pi fL$.

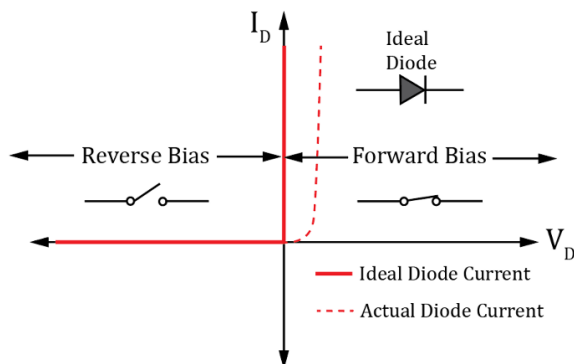
Power $P = VI = I^2R = V^2/R$. Average AC Power $P = V_{rms}I_{rms} \cos(\theta)$.



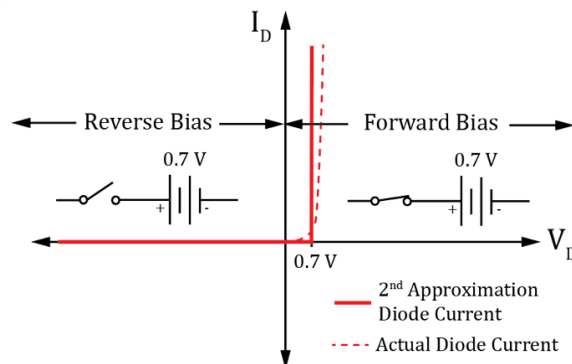
Shockley Diode Equation: $I_D = I_S(e^{V_D/nV_T} - 1) A$, where I_S is the reverse saturation current, V_D is applied voltage across the Diode, V_T is referred to as the thermal voltage, and n is an ideality factor ranging from 1 - 2. Assume $n = 1$ for ECEN 350.

Thermal Voltage: $V_T = \frac{kT_K}{q}$, where $k = 1.38 \times 10^{-23} J/K$ is Boltzmann's constant, T_K is the temperature in Kelvin, and $q = 1.6 \times 10^{-19} C$ is the magnitude of the charge of an electron or proton. $V_T \approx 25 mV @ 20^\circ C$.

Ideal Diode Model – 1st Approximation

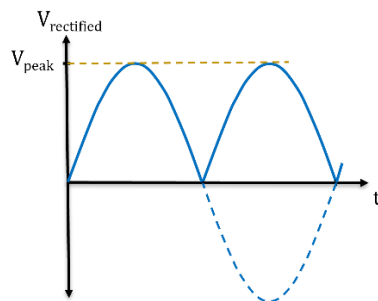
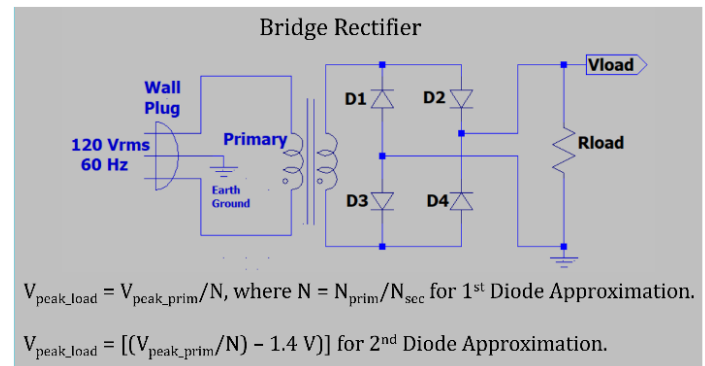
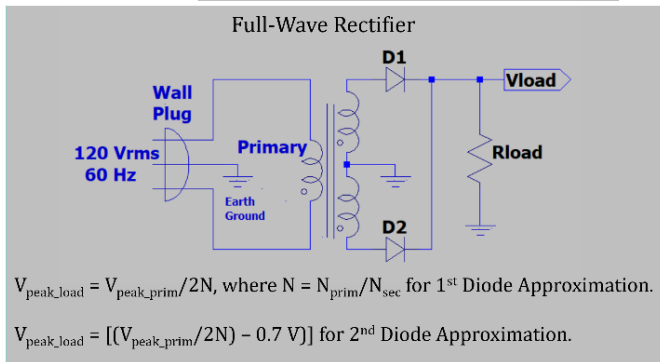
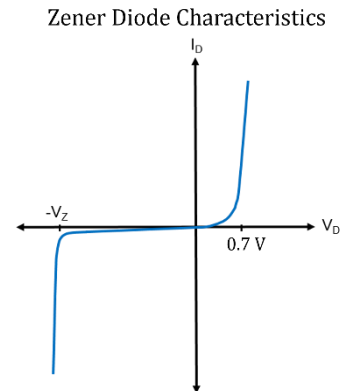
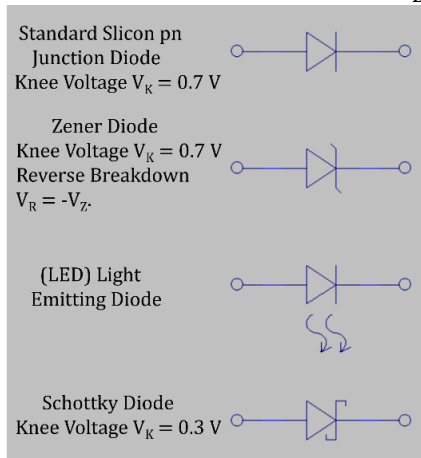


2nd Approximation for Silicon pn Junction Diode Simplified Diode Model

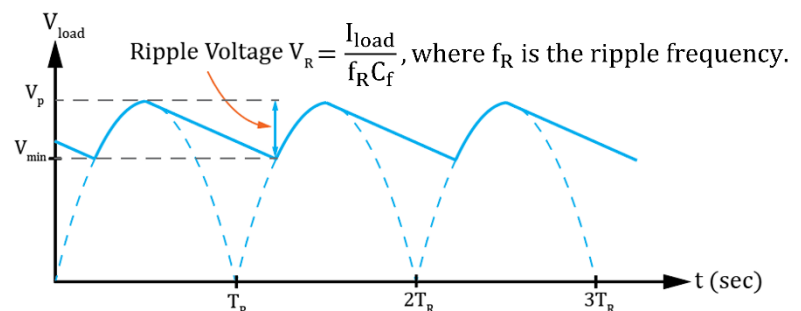


Junction Temperature: $T_J = T_A + \Delta T_J = T_A + PR_{\theta JA}$. $T_J = T_A + PR_{\theta JA}$, where T_A is the ambient temperature, P is the power dissipated, and $R_{\theta JA}$ is the thermal resistance in $^{\circ}\text{C}/\text{W}$.

Diode DC Forward Resistance, $R_F = \frac{V_D}{I_D}$. Diode Bulk Resistance, $R_B = \frac{\Delta V_D}{\Delta I_D}$.



The Above Full-Wave Rectified Waveform has the Following Values:
 $V_{\text{avg}} = 0.637(V_{\text{peak}})$. $V_{\text{rms}} = 0.707(V_{\text{peak}})$.



The ripple frequency $f_R = 1/T_R$, is twice the frequency (half the period) of the non-rectified input waveform.

